



Shenzhen Tuofeng Semiconductor Technology Co., Ltd

TO-92 Plastic-Encapsulate Transistors

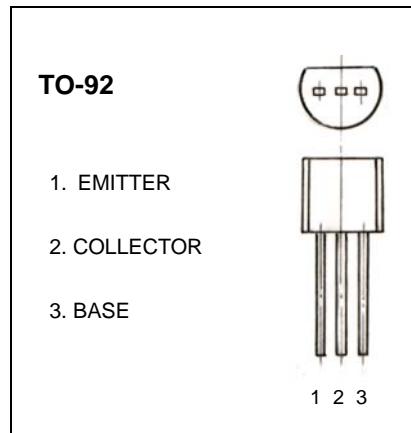
A733 TRANSISTOR(PNP)

FEATURE

Power dissipation

MAXIMUM RATINGS* T_A=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-60	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-100	mA
P _D	Total Device Dissipation	250	mW
T _J	Junction Temperature	150	°C
T _{stg}	Junction and Storage Temperature	-55-150	°C



*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

ELECTRICAL CHARACTERISTICS(T_{amb}=25°C unless otherwise specified)

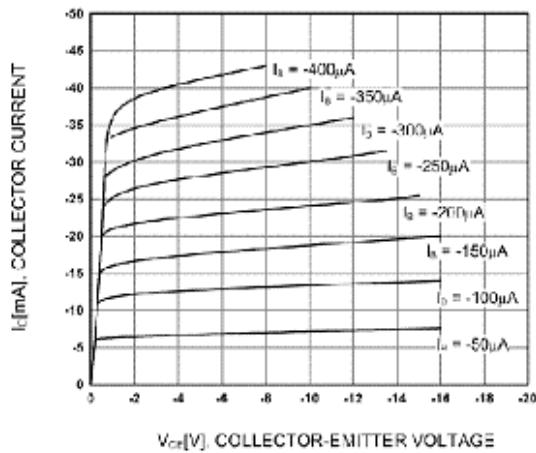
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR) _{CBO}	I _C = -50uA, I _E =0	-60			V
Collector-emitter breakdown voltage	V(BR) _{CEO}	I _C = -1mA, I _B =0	-50			V
Emitter-base breakdown voltage	V(BR) _{EBO}	I _E = -50uA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -60 V , I _E =0			-0.1	uA
Emitter cut-off current	I _{EBO}	V _{EB} = -5 V , I _C =0			-0.1	uA
DC current gain	h _{FE}	V _{CE} = -6 V, I _C = -1mA	90	200	600	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -100mA, I _B =- 10mA		-0.18	-0.3	V
Base-emitter voltage	V _{BE}	V _{CE} =-6V, I _C =-1.0mA	-0.58	-0.62	-0.68	V
Transition frequency	f _T	V _{CE} =-6V, I _C =-10mA	100	180		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		4.5	6	pF
Noise figure	NF	V _{CE} =-6V, I _C =-0.3mA, R _g =10kΩ, f=100Hz		6	20	dB

CLASSIFICATION OF h_{FE}

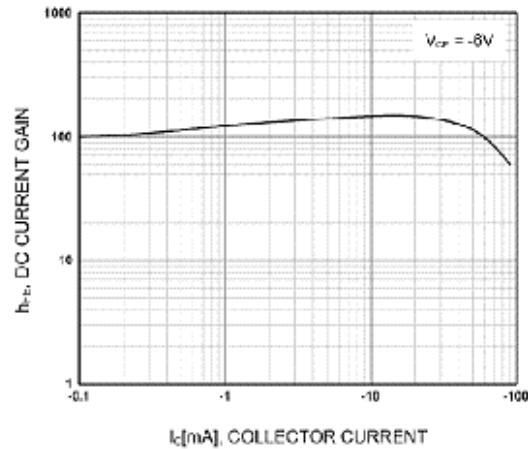
Rank	R	Q	P	K
Range	90-180	135-270	200-400	300-600

Typical Characteristics

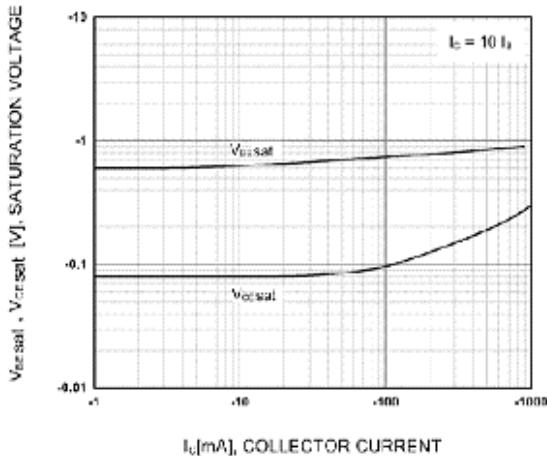
A733



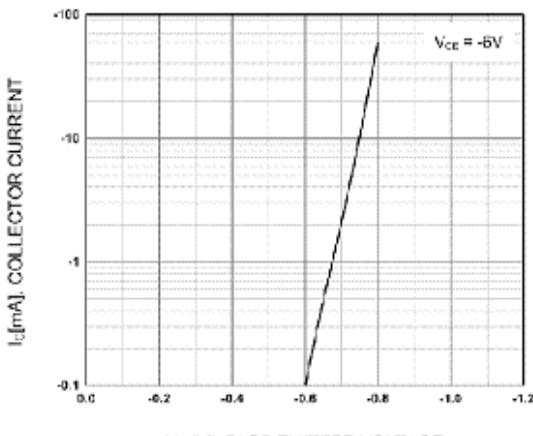
Static Characteristic



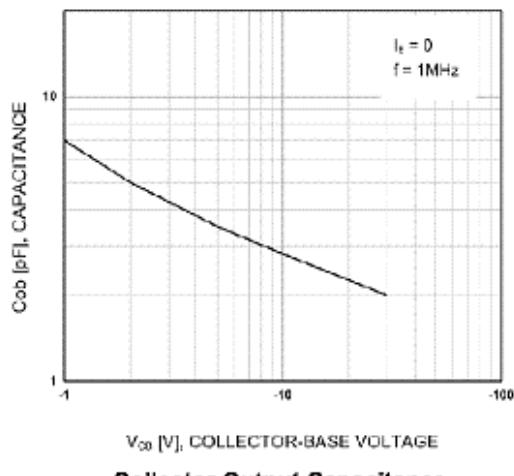
DC current Gain



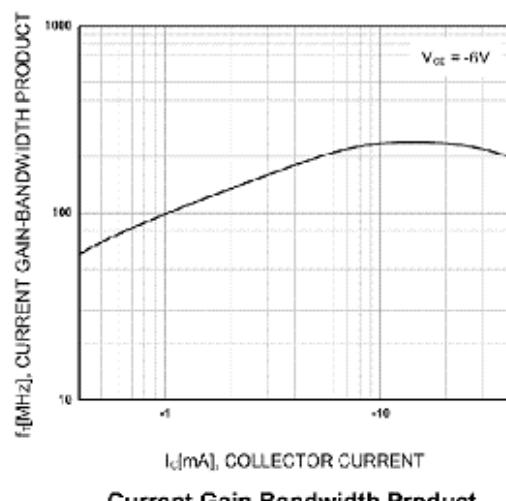
**Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage**



Base-Emitter On Voltage



Collector Output Capacitance



Current Gain Bandwidth Product